Product Overview

FFSP1265A: SiC Diode - 650V, 12A, TO-220-2

For complete documentation, see the data sheet.

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability to silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175 °C
- High Surge Current Capacity
- Positive Temperature Coefficient
- No Reverse Recovery / No Forward Recovery

Applications

- PFC
- Industrial Power
- Solar
- EV Charger
- UPS

Part Electrical Specifications

Product	Compliance	Status	Device Grade	Configuration	V_{RRM} (V)	$I_{F(ave)}$ (A)	V_F (Max)	I_{FSM} (A)	I_R (Max) (µA)	Package Type
FFSP1265A	Pb-free Halide free	NEW	Commercial	Single	650	12	1.75	70	200	TO-220-2

For more information please contact your local sales support at www.onsemi.com.

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